SiSH112DN

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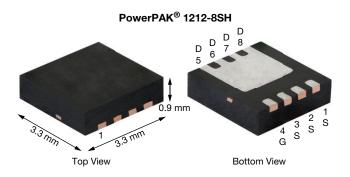
RoHS

COMPLIANT

HALOGEN

FREE

N-Channel 30 V (D-S) Fast Switching MOSFET



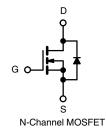
PRODUCT SUMMARY						
V _{DS} (V)	30					
$R_{DS(on)}$ max. (Ω) at V_{GS} = 10 V	0.0075					
$R_{DS(on)}$ max. (Ω) at V_{GS} = 4.5 V	0.0082					
Q _g typ. (nC)	18					
I _D (A)	17.8					
Configuration	Single					

FEATURES

- TrenchFET[®] power MOSFET
- 100 % R_g tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Synchronous rectification
- Load switch



ORDERING INFORMATION	
Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	SiSH112DN-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless	s otherwise no	oted)			
PARAMETER		SYMBOL	10 S	STEADY STATE	UNIT	
Drain-source voltage		V _{DS}	30	30	V	
Gate-source voltage		V _{GS}	±12	±12	v	
Continuous drain current (T _J = 150 °C) ^a	T _C = 25 °C	- I _D	17.8	11.3		
	T _C = 70 °C		14.2	9.1		
Pulsed drain current		I _{DM}	60	60	A	
Continuous source current (diode conduction) ^a		I _S	3.2	1.3		
Single avalanche current		I _{AS}	20	20		
Single avalanche energy	, L = 0.1 mH		20	20	mJ	
Maximum newer discipation a	T _C = 25 °C	D	3.8	1.5	14/	
Maximum power dissipation ^a	T _C = 70 °C	P _D	2	0.8	W	
Operating junction and storage temperature range		T _J , T _{stg}	-50 to +150		ŝ	
Soldering recommendations (peak temperature) b, c		-	260		°C	

Notes

a. Surface mounted on 1" x 1" FR4 board

b. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 1212-8SH is a leadless package within the PowerPAK 1212-8 package family. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

c. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum junction-to-ambient ^a	$t \le 10 s$	D	24	33		
Maximum junction-to-ambient ~	Steady state	R _{thJA}	65	81	°C/W	
Maximum junction-to-foot (drain)	Steady state	R _{thJC}	1.9	2.4		

Note

a. Surface mounted on 1" x 1" FR4 board

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static			•				
Gate threshold voltage	te threshold voltage $V_{GS(th)}$ $V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$		0.6	-	1.5	V	
Gate-body leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 12 V$	-	-	±100	nA	
Zava anto valtago duoin ovument		$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1	μA	
Zero gate voltage drain current	I _{DSS}	V_{DS} = 30 V, V_{GS} = 0 V, T_{J} = 55 °C	-	-	5		
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	40	-	-	А	
	D	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 17.8 \text{ A}$	-	0.0060	0.0075	Ω	
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 17 \text{ A}$	-	0.0065	0.0082		
Forward transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 17.8 \text{ A}$	-	97	-	S	
Diode forward voltage ^a	V _{SD}	$I_{\rm S} = 3.2$ A, $V_{\rm GS} = 0$	-	0.7	1.2	V	
Dynamic ^b			•				
Input capacitance	C _{iss}		-	2610	-		
Output capacitance	C _{oss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		340	-	pF	
Reverse transfer capacitance	C _{rss}		-	145	-		
Total gate charge	Qg		-	18	27		
Gate-source charge	Q _{gs}	V_{DS} = 15 V, V_{GS} = 4.5 V, I_{D} = 17.8 A	-	6.2	-	nC	
Gate-drain charge	Q _{gd}		-	3.1	-	1	
Gate resistance	Rg	f = 1 MHz	0.5	1.2	1.8	Ω	
Turn-on delay time	t _{d(on)}		-	10	15		
Rise time	tr	$V_{DD} = 15 \text{ V}, \text{ R}_{\text{L}} = 15 \Omega$	-	10	15	ns	
Turn-off delay time	t _{d(off)}	$I_D \cong 1 \text{ A}, V_{\text{GEN}} = 10 \text{ V}, R_g = 6 \Omega$	-	65	100		
Fall time	t _f		-	10	15		
Body diode reverse recovery time	t _{rr}		-	30	60		
Body diode reverse recovery charge	Q _{rr}	I _F = 3.2 A, di/dt = 100 A/μs	-	18	-	nC	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

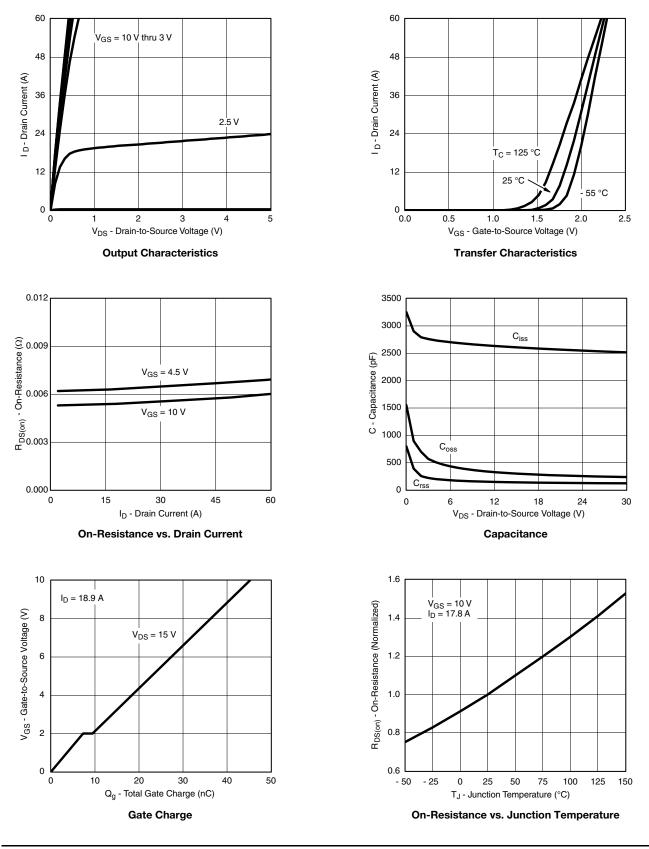
b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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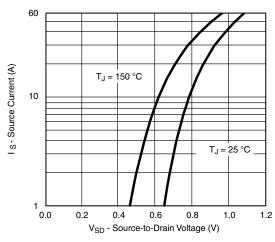
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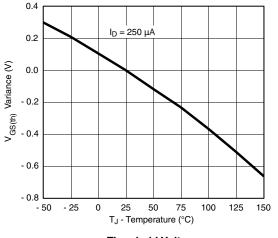
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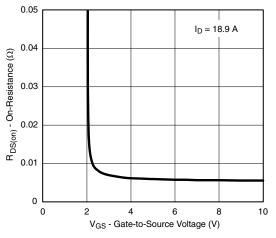
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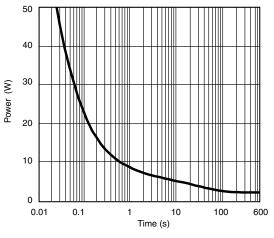
Source-Drain Diode Forward Voltage



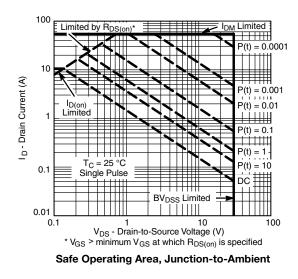
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



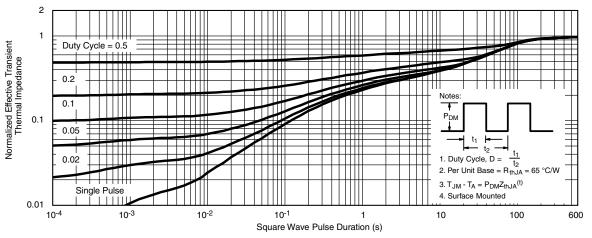
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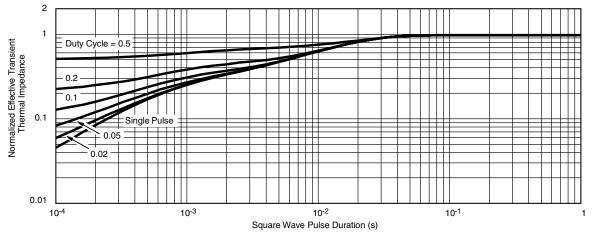
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Normalized Thermal Transient Impedance, Junction-to-Ambient

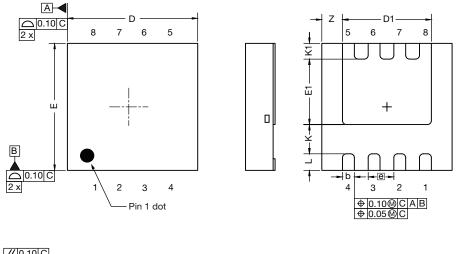


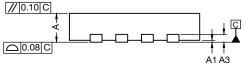
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?79345.



Case Outline for PowerPAK[®] 1212-SWLH and PowerPAK[®] 1212-8SH





DIM.		MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
А	0.82	0.90	0.98	0.032	0.035	0.038		
A1	0.00	-	0.05	0.000	-	0.002		
A3		0.20 ref.	•		0.008 ref.			
b	0.25	0.30	0.35	0.010	0.012	0.014		
D	3.20	3.30	3.40	0.126	0.130	0.134		
D1	2.15	2.25	2.35	0.085	0.089	0.093		
E	3.20	3.30	3.40	0.126	0.130	0.134		
E1	1.60	1.70	1.80	0.063	0.067	0.071		
е		0.65 bsc.			0.026 bsc.			
К	0.76 ref.			0.030 ref.				
K1	0.41 ref.			0.016 ref.				
L	0.33	0.43	0.53	0.013	0.017	0.021		
Z	0.525 ref.			0.021 ref.				



RECOMMENDED MINIMUM PADS FOR PowerPAK[®] 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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